TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP281,TLP281-4

PROGRAMMABLE CONTROLLERS AC/DC-INPUT MODULE PC CARD MODEM(PCMCIA)

TLP281 and TLP281-4 is a very small and thin coupler, suitable for surface mount assembly in applications such as PCMCIA Fax modem, programmable controllers.

TLP281 and TLP281-4 consist of photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

Collector-Emitter Voltage : 80 V (MIN)
 Current Transfer Ratio : 50% (MIN)
 Rank GB : 100% (MIN)
 Isolation Voltage : 2500 Vrms (MIN)

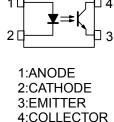
UL Recognized : UL1577 , File No. E67349
 BSI Approved : BS EN 60065: 1994,
 : BS EN 41003: 1997

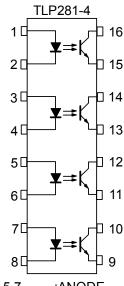
Certificate No. 8143, 8144

Unit in mm TLP281 1 2 2.6 ± 0.25 0.4 ± 0.1 1.27 ± 0.2 Half Pilch Mini Flet 4 pin

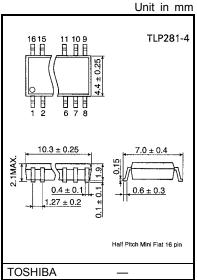
Weight: 0.05 g

PIN CONFIGURATION(Top view)





1,3,5,7 :ANODE 2,4,6,8 :CATHODE 9,11,13,15 :EMITTER 10,12,14,16 :COLLECTOR



Weight: 0.19 g

TYPE	Classi- Fication(*1)	(I _C I _F = 5 mA, V _{CE}	fer Ration (%) / I _F) = 5 V, Ta = 25°C	Marking of Classification
		Min	Max	
	Blank 50 600		Blank ,Y ,YE,G,G ,GR,B,BL,GB	
	Rank Y	50	150	YE
	Rank GR	100	300	GR
	Rank BL	200	600	BL
TLP281	Rank GB	100	600	GB
	Rank YH	75	150	Y*
	Rank GRL	100	200	G
	Rank GRH	150	300	g [•]
	Rank BLL	200	400	В
TLP281-4	Blank	50	600	Blank , GB
TLI 201-4	Rank GB	100	600	GB

^{*1:} Ex. rank GB: TLP281 (GB)

(Note): Application type name for certification test, please use standard product type name, i.e. TLP281 (GB): TLP281-1, TLP281-4 (GB): TLP281-4

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		OVMDOL	RAT	UNIT	
		SYMBOL	TLP281	TLP281-4	UNIT
Forward Current		lF	50		mA
	Forward Current Derating	ΔI _F /°C	-0.7 (Ta≥53°C)	-0.5 (Ta≥25°C)	mA /°C
LED	Pulse Forward Current	I _{FP}	1		Α
	Reverse Voltage	V_{R}	Ę	5	٧
	Junction Temperature	Tj	12	°C	
	Collector-Emitter Voltage	V_{CEO}	8	0	V
	Emitter-Collector Voltage	V _{ECO}	7	٧	
OR	Collector Current	I _C	50		mA
DETECTOR	Collector Power Dissipation (1 Circuit)	PC	150	100	mW
JG.	Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit)	ΔP _C /°C	-1.5	-1.0	mW /°C
	Junction Temperature	Tj	12	25	°C
Оре	erating Temperature Range	T _{opr}	-55~100		°C
Sto	rage Temperature Range	T _{stg}	-55~125		°C
Lea	d Soldering Temperature	T _{sol}	260 (10s)		°C
Total Package Power Dissipation (1 Circuit)		P _T	200	170	mW
	al Package Power Dissipation ating (Ta≥25°C) (1 Circuit)	ΔP _T /°C	-2.0	-1.7	mW /°C
Isol	ation Voltage (Note1)	BVS	2500(AC,1min,R.H.≤60%)		Vrms

(Note1)Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I _R	V _R = 5 V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
DETECTOR	Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C = 0.5 mA	80	_	_	V
	Emitter-Collector Breakdown Voltage	V _{(BR) ECO}	I _E = 0.1 mA	7	_	_	٧
	Collector Dark Current	loso	V _{CE} = 48 V, Ambient Light Below (100 tx)	_	0.01 (2)	0.1 (10)	μΑ
	(Note:	P) ICEO	V _{CE} = 48 V, Ta = 85°C Ambient Light Below (100 ℓx)	_	2 (4)	50 (50)	μΑ
	Capacitance (Collector to Emitter)	C _{CE}	V = 0, f = 1 MHz	_	10	_	pF

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(Note 2) Because of the construction,leak current might be increased by ambient light.

Please use photocoupler with less ambient light.

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V	50	_	600	- %
Current transfer Natio		Rank GB	100	_	600	
Saturated CTR	I _C / I _{F (sat)}	IF = 1 mA, VCE = 0.4 V	_	60	_	%
Saturated CTIX		Rank GB	30	_	_	/0
Collector-Emitter		I _C = 2.4 mA, I _F = 8 mA	ı	_	0.4	
Saturation Voltage	V _{CE (sat)}	I _C = 0.2 mA, I _F = 1 mA	-	0.2	_	V
Catalation Voltage		Rank GB	_	_	0.4	
Off-State Collector Current	I _{C (off)}	V _F = 0.7 V, V _{CE} = 48 V		_	10	μA

ISOLATION CHARACTERISTICS (Ta = 25°C)

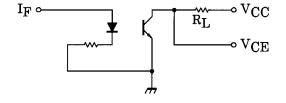
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C _S	V _S = 0 V, f = 1 MHz	_	0.8		pF
Isolation Resistance	R _S	V _S = 500 V, R.H.≤60%	5×10 ¹⁰	10 ¹⁴	-	Ω
	BVS	AC , 1 minute	2500	_	_	Vrms
Isolation Voltage		AC , 1 second,in OIL	_	5000	_	VIIIIS
		DC , 1 minute, in OIL	_	5000	_	Vdc

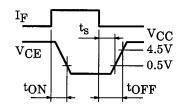
SWITCHING CHARACTERISTICS (Ta = 25°C)

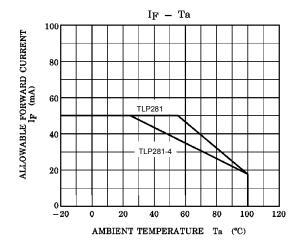
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t _r		_	2	_	
Fall Time	t _f	V _{CC} = 10 V, I _C = 2 mA	_	3	_	μs
Turn-On Time	t _{on}	$R_L = 100\Omega$	_	3	_	μο
Turn-Off Time	t _{off}		_	3	_	
Turn-On Time	t _{ON}	R_L = 1.9 kΩ (Fig.1) V_{CC} = 5 V, I_F = 16 mA	_	2	_	
Storage Time	ts		_	25	_	μs
Turn-Off Time	t _{OFF}		_	40	_	

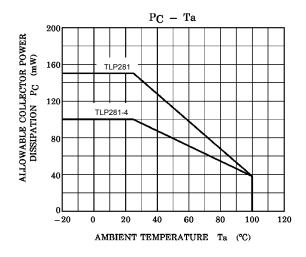
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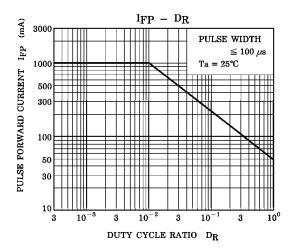
(Fig.1)SWITCHING TIME TEST CIRCUIT

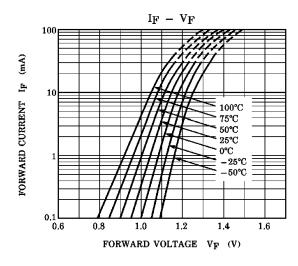


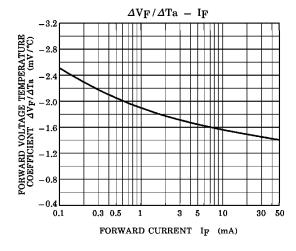


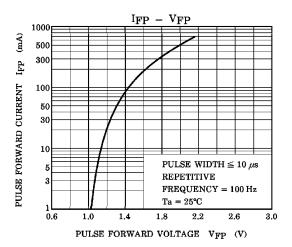


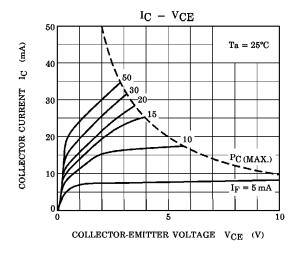


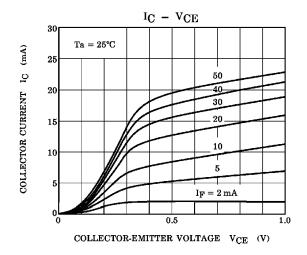


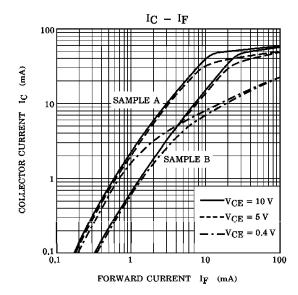


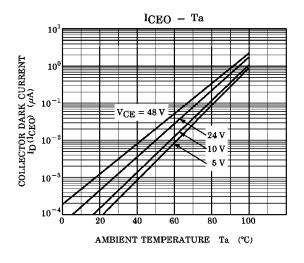


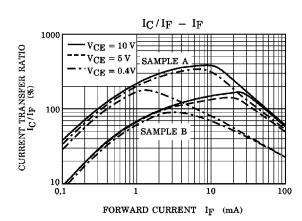




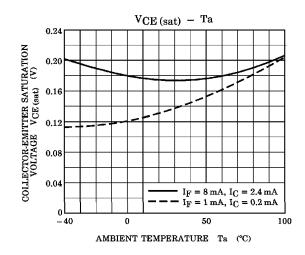


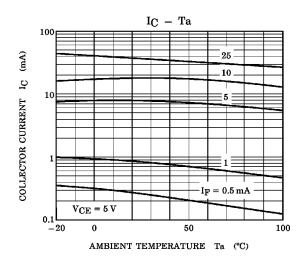


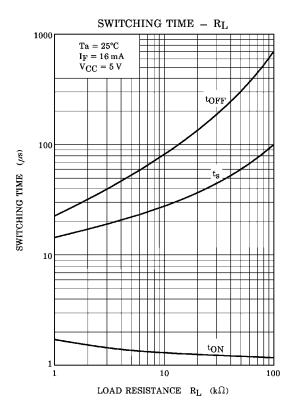


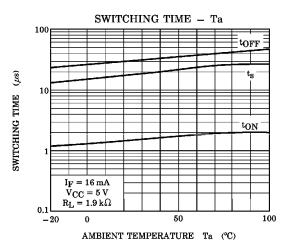


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